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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number: 10/802,566
Filing Date: 03-17-2004
First Named Inventor: **MOU-SHIUNG LIN**
Art Unit: 2892
Examiner Name: **AJAY ARORA**

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Attorney Docket No: 085027-0109

US PATENT DOCUMENTS

Examiner Initial *	Cite No	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or RelevantFigures Appear
		NONE			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or RelevantFigures Appear	T[2]
		NONE				

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	2	EDELSTEIN, D.C., "Advantages of Copper Interconnects," Proceedings of the 12th International IEEE VLSI Multilevel Interconnection Conference (1995) pgs. 301-307	
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	5	YEOH, A. et al. "Copper Die Bumps (First Level Interconnect) and Low-K Dielectrics in 65nm High Volume Manufacturing," Electronic Components and Technology Conference (2006) pgs. 1611-1615	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AA/

EXAMINER /Ajay Arora/ **DATE CONSIDERED** 01/01/2011

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[1] EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [2] Applicant's unique citation designation number (optional). [3] Applicant is to place a check mark here if English language Translation is attached

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